



Amend #12/C
w/ RCE
15.45/6059
Robinson
7/2/03
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:)
TAKEUCHI)
Serial No. 09/930,365)
Filed: August 15, 2001)
For: METHODS FOR MANUFACTURING)
SEMICONDUCTOR DEVICES AND)
SEMICONDUCTOR DEVICES HAVING)
TRENCH ISOLATION REGIONS)

Group Art Unit: 2810G1 CENTER 2800
Examiner: Vu, Quang D.

AMENDMENT

Mail Stop RCE
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In response to the Office Action dated March 14, 2003, the response being due by Monday, June 16, 2003, applicant has filed a Request for Continued Examination (RCE) together with this paper. Please enter and consider the following.

IN THE CLAIMS:

Please enter the following claim set:

1-19 (canceled)

20. (currently amended) A method as in claim 24 ~~19~~, wherein the first layer
C1 comprises an epitaxial growth layer.

21. (currently amended) A method as in claim 24 ~~19~~, further comprising removing
the polishing stopper layer after planarizing the dielectric layer.

22. (currently amended) A method as in claim 24 ~~19~~, further comprising oxidizing
at least a portion of the first layer in the at least one trench prior to forming the dielectric layer in
and above the trench.